

/ Descriptions

WR0459I M M E QSQ æ M ç s ll 1 Silicon NPN transistor in a TO-126F Plastic Package.

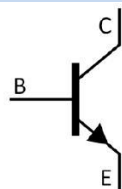
/ Features

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Low $V_{CE(sat)}$, high current and high f_T , excellent linearity of h_{FE} , fast switching time.

/ Applications

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Relay drivers, high-speed inverters, general high-current switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	100 200	160 320	200 400

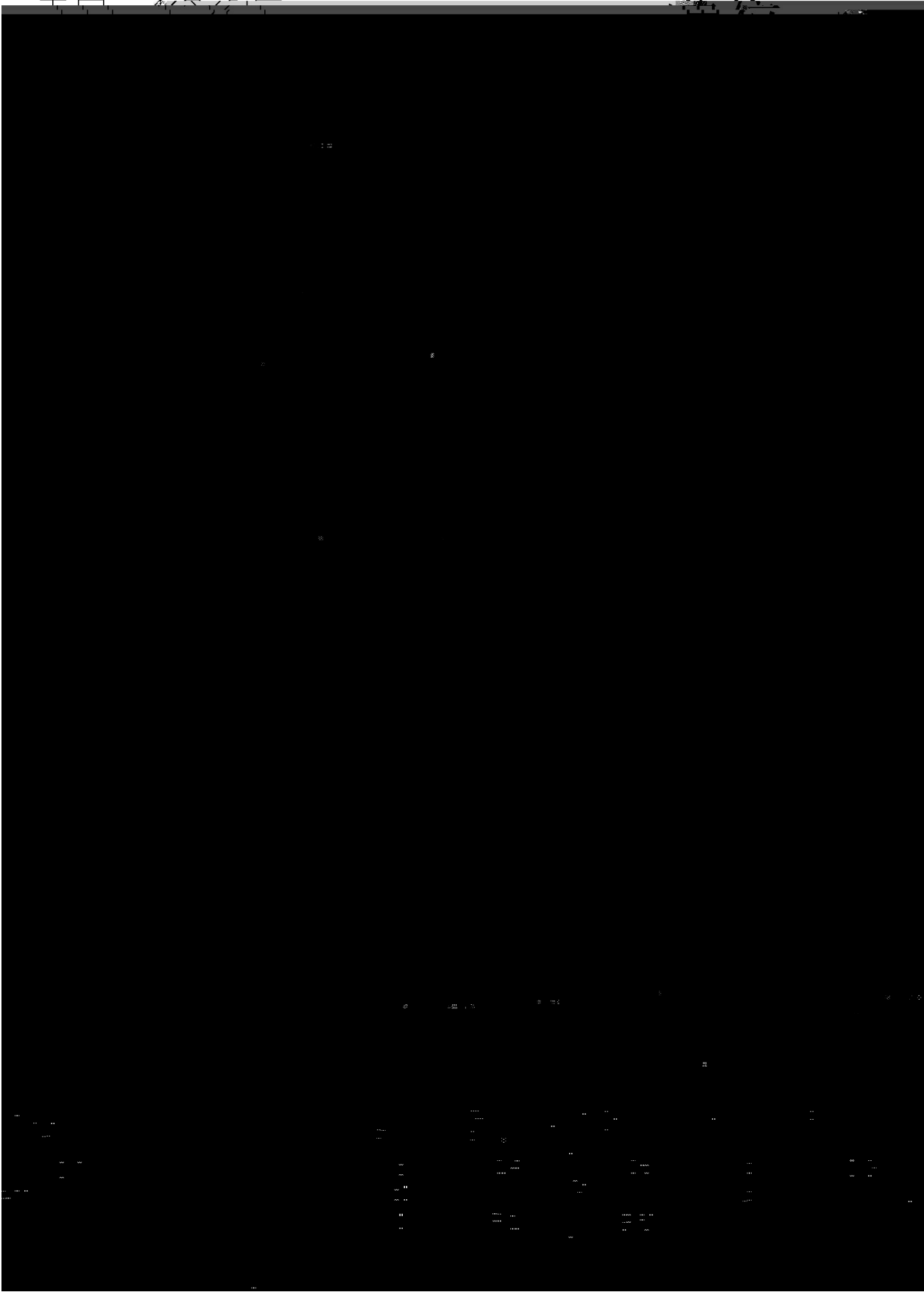
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=125^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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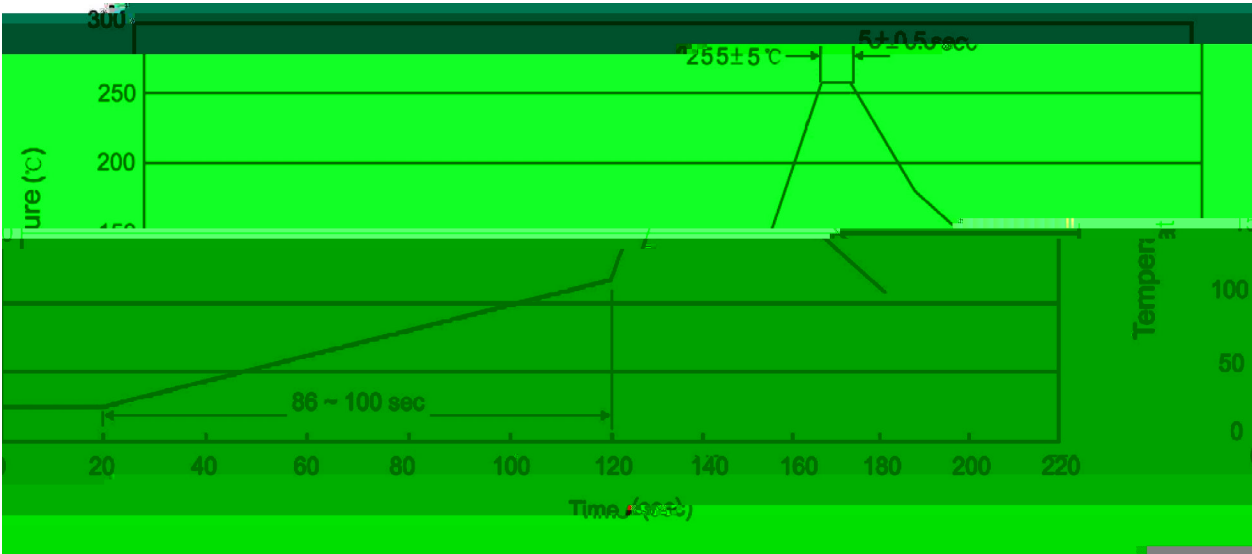
/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for Dip Soldering(Pb-Free)



- 说明

 1. 预加热: 25~150 °C, 时间: 60~90sec;
 2. 峰值温度: 255±5 °C, 持续时间: 5±0.5sec;
 3. 冷却速度: 2~10 °C/sec.
- Note:

 - 1.Preheating:25~150 °C, Time:60~90sec.
 - 2.Peak Temp.:255±5 °C, Duration:5±0.5sec.
 3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5 °C 时间: 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

包装形式 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	